

**Dual N-Channel Logic Level Enhancement Mode Power MOSFET**

# MTB45A06Q8

BV <sub>DSS</sub>	60V
I <sub>D</sub>	6A
R <sub>DS(ON)(MAX.)</sub>	45mΩ

**Description**

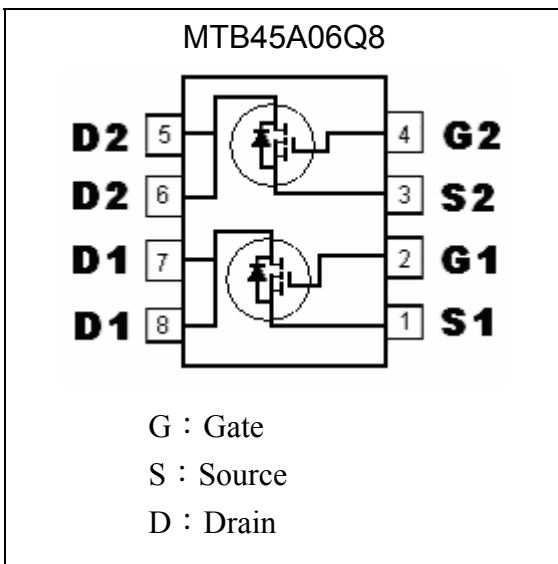
The MTB45A06Q8 provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.

The SOP-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

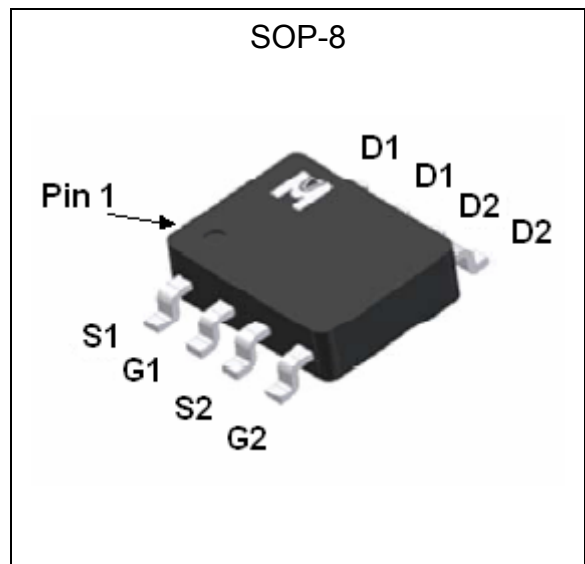
**Features**

- R<sub>DS(ON)</sub>=45mΩ @V<sub>GS</sub>=10V, I<sub>D</sub>=6A
- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Dual N-ch MOSFET package
- Pb-free and Halogen-free package

**Equivalent Circuit**



**Outline**





**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V <sub>DS</sub>	60	V	
Gate-Source Voltage	V <sub>GS</sub>	±20		
Continuous Drain Current @ T <sub>C</sub> =25°C	I <sub>D</sub>	6	A	
Continuous Drain Current @ T <sub>C</sub> =100°C		4.5		
Pulsed Drain Current		24 *1		
Avalanche Current	I <sub>AS</sub>	15		
Avalanche Energy @ L=0.1mH, I <sub>D</sub> =6A, R <sub>G</sub> =25Ω	E <sub>AS</sub>	7.2	mJ	
Repetitive Avalanche Energy @ L=0.05mH	E <sub>AR</sub>	3.6 *2		
Total Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.4	W
		T <sub>A</sub> =100°C	1.3	
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55~+175	°C	

100% UIS testing in condition of V<sub>D</sub>=30V, L=0.1mH, V<sub>G</sub>=10V, I<sub>L</sub>=10A, Rated V<sub>DS</sub>=60V N-CH

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R <sub>th,j-c</sub>	25	°C/W
Thermal Resistance, Junction-to-ambient, max	R <sub>th,j-a</sub>	62.5 *3	°C/W

- Note : 1. Pulse width limited by maximum junction temperature  
 2. Duty cycle ≤ 1%  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, 125°C/W when mounted on minimum copper pad

**Characteristics (Tc=25°C, unless otherwise specified)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
BV <sub>DSS</sub>	60	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =250μA
V <sub>GS(th)</sub>	1.0	2.0	3.2	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA
G <sub>FS</sub> *1	-	15	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =5A
I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> =±20
I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =48V, V <sub>GS</sub> =0
	-	-	25		V <sub>DS</sub> =40V, V <sub>GS</sub> =0, T <sub>j</sub> =125°C
I <sub>D(ON)</sub> *1	5	-	-	A	V <sub>DS</sub> =5V, V <sub>GS</sub> =10V
R <sub>DS(ON)</sub> *1	-	40	45	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =6A
	-	55	70	mΩ	V <sub>GS</sub> =5V, I <sub>D</sub> =5A
<b>Dynamic</b>					
C <sub>iss</sub>	-	1213	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1MHz
C <sub>oss</sub>	-	86	-		
C <sub>rss</sub>	-	70	-		



**Characteristics (Tc=25°C, unless otherwise specified)**

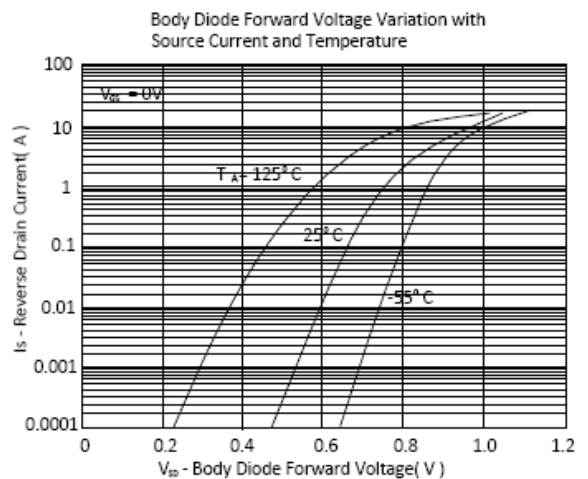
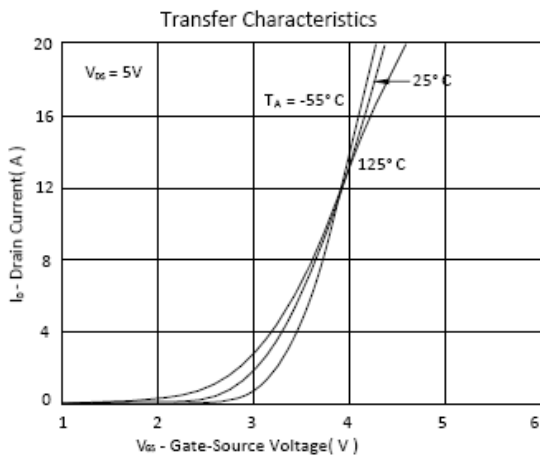
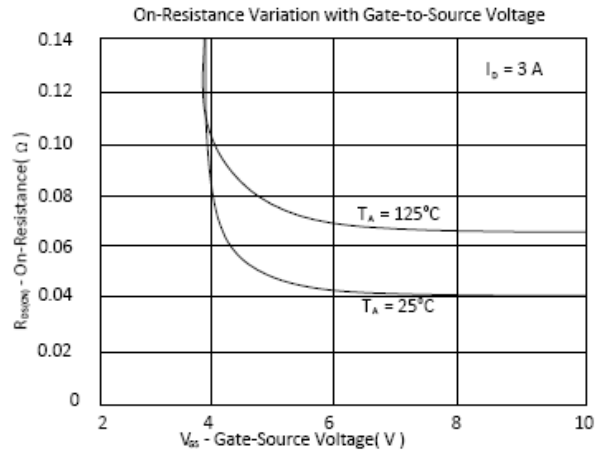
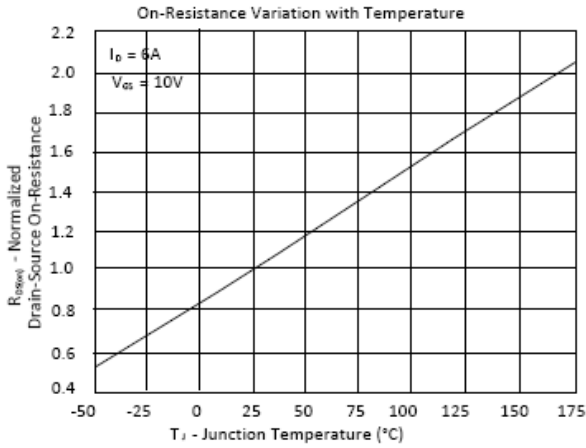
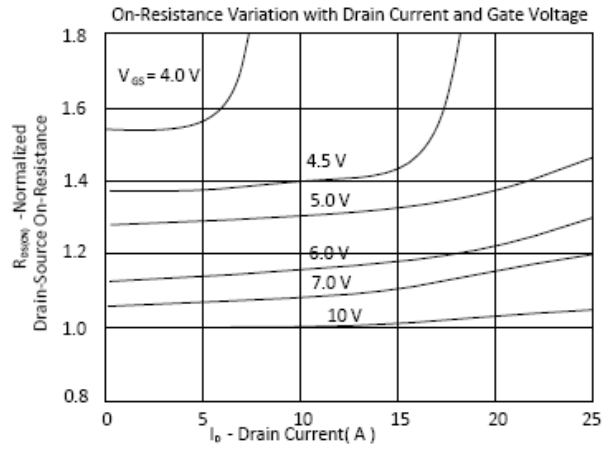
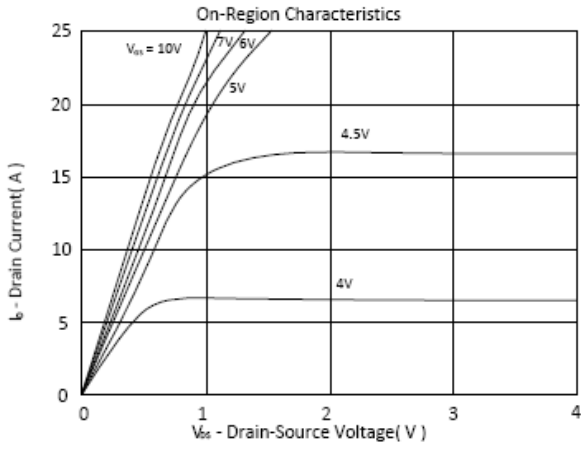
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Qg *1, 2	-	12	-	nC	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A
Qgs *1, 2	-	2.5	-		
Qgd *1, 2	-	2.6	-		
t <sub>d(ON)</sub> *1, 2	-	12	-	ns	V <sub>DS</sub> =30V, I <sub>D</sub> =1A, V <sub>GS</sub> =10V, R <sub>GS</sub> =6Ω
t <sub>r</sub> *1, 2	-	8	-		
t <sub>d(OFF)</sub> *1, 2	-	20	-		
t <sub>f</sub> *1, 2	-	7	-		
<b>Source-Drain Diode</b>					
I <sub>S</sub> *1	-	-	2.3	A	
I <sub>SM</sub> *3	-	-	9.2		
V <sub>SD</sub> *1	-	-	1.2	V	I <sub>F</sub> =I <sub>S</sub> , V <sub>GS</sub> =0V

Note : \*1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%  
 \*2.Independent of operating temperature  
 \*3.Pulse width limited by maximum junction temperature.

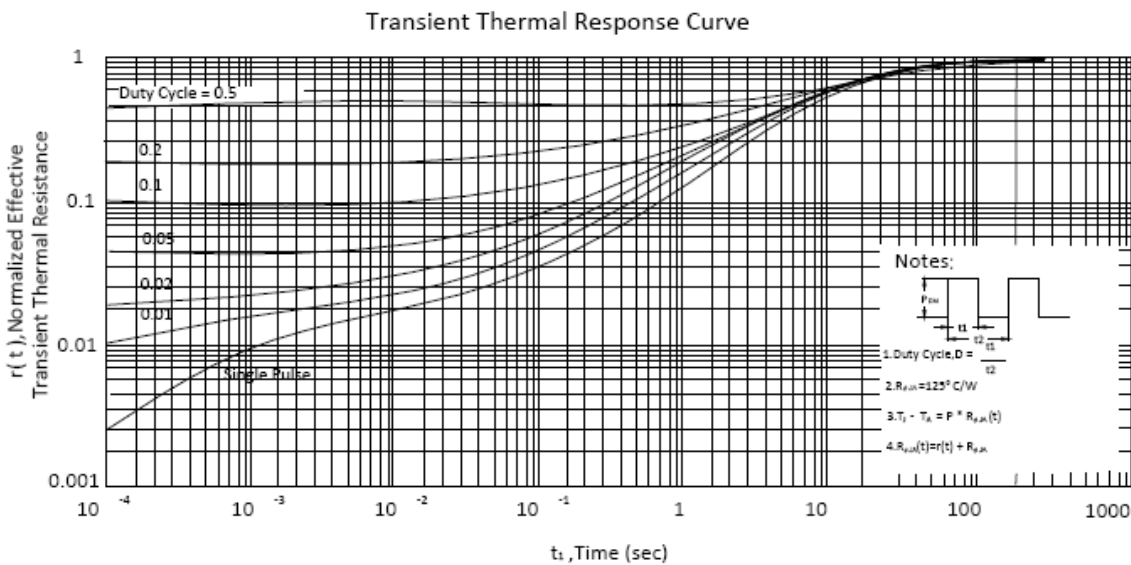
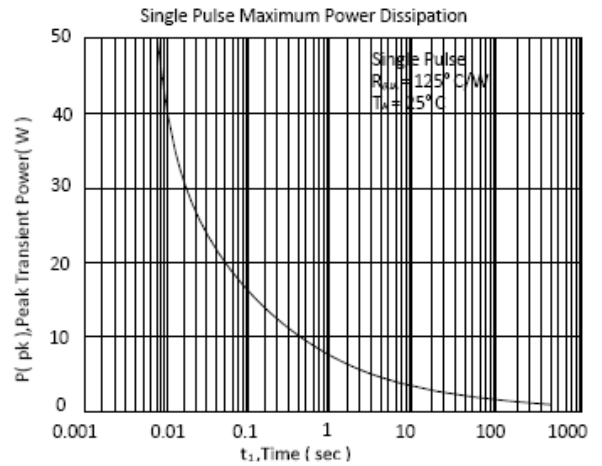
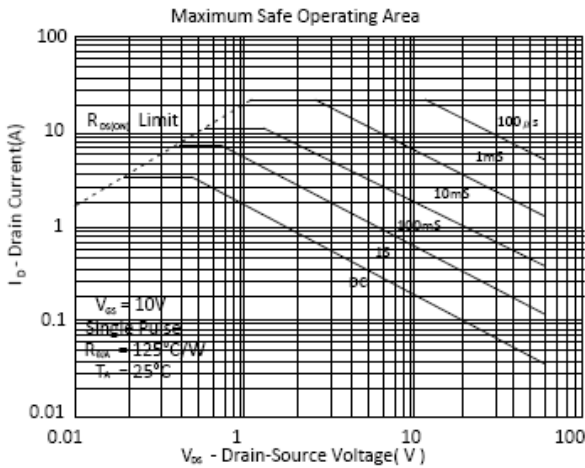
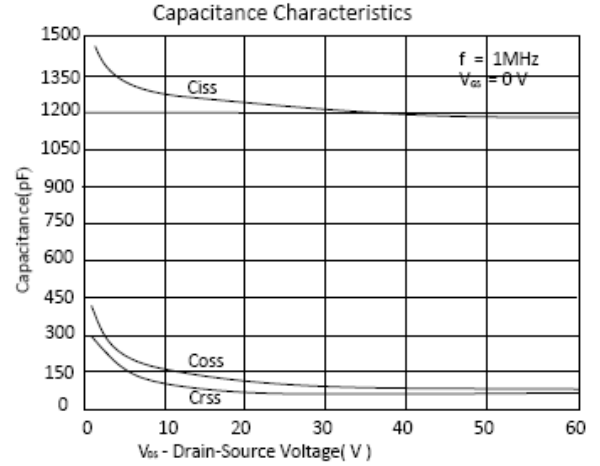
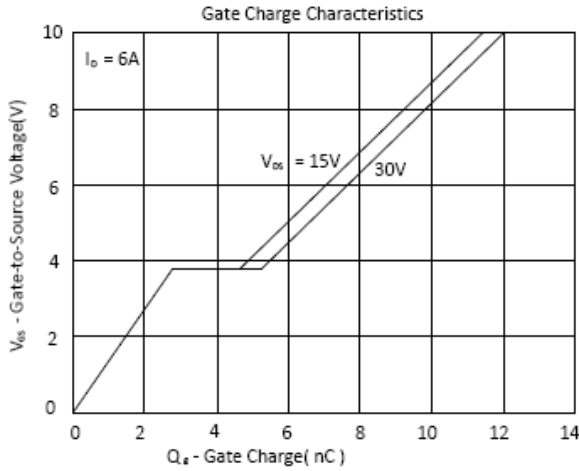
**Ordering Information**

Device	Package	Shipping	Marking
MTB45A06Q8	SOP-8 (Pb-free & Halogen-free package)	2500 pcs / Tape & Reel	B45A06

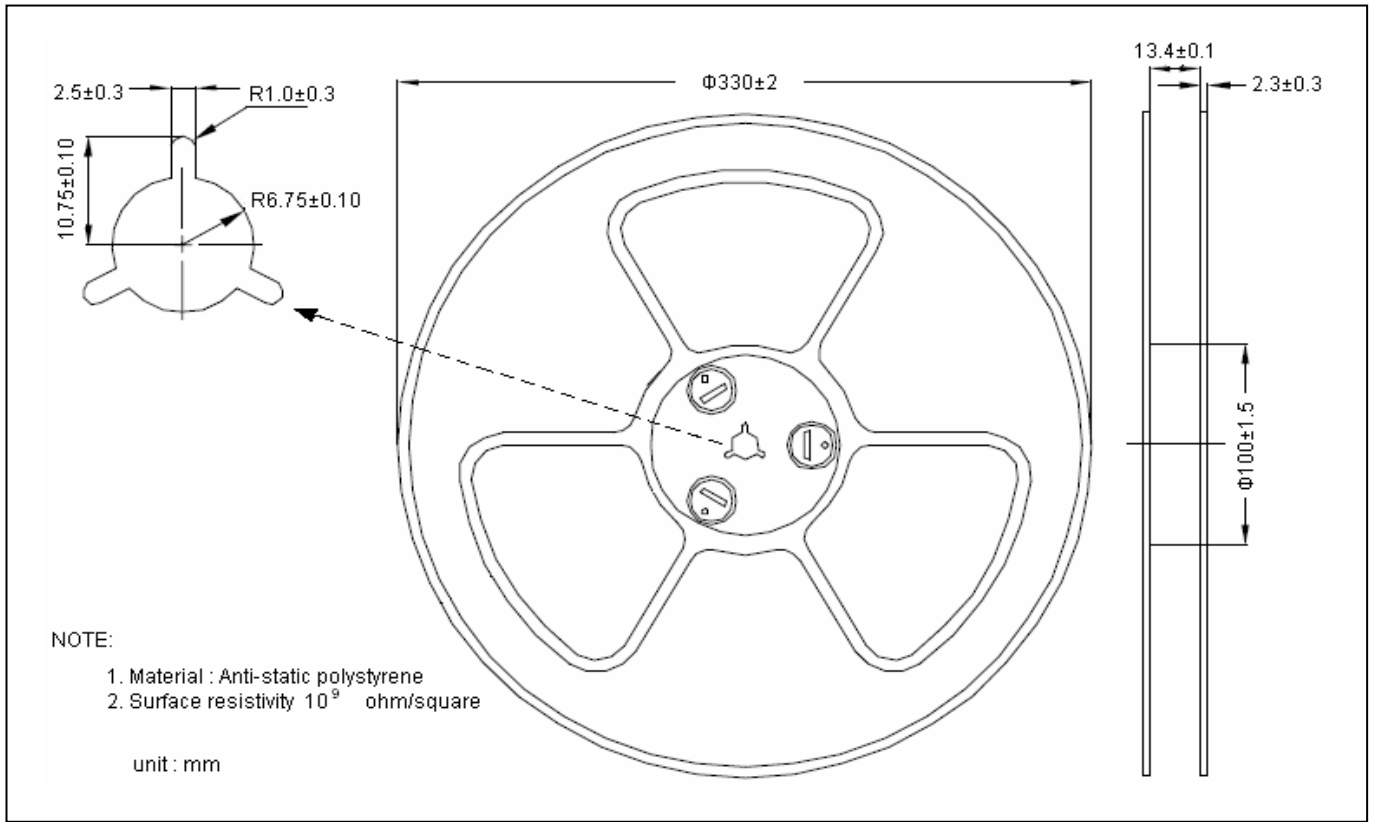
**Characteristic Curves**



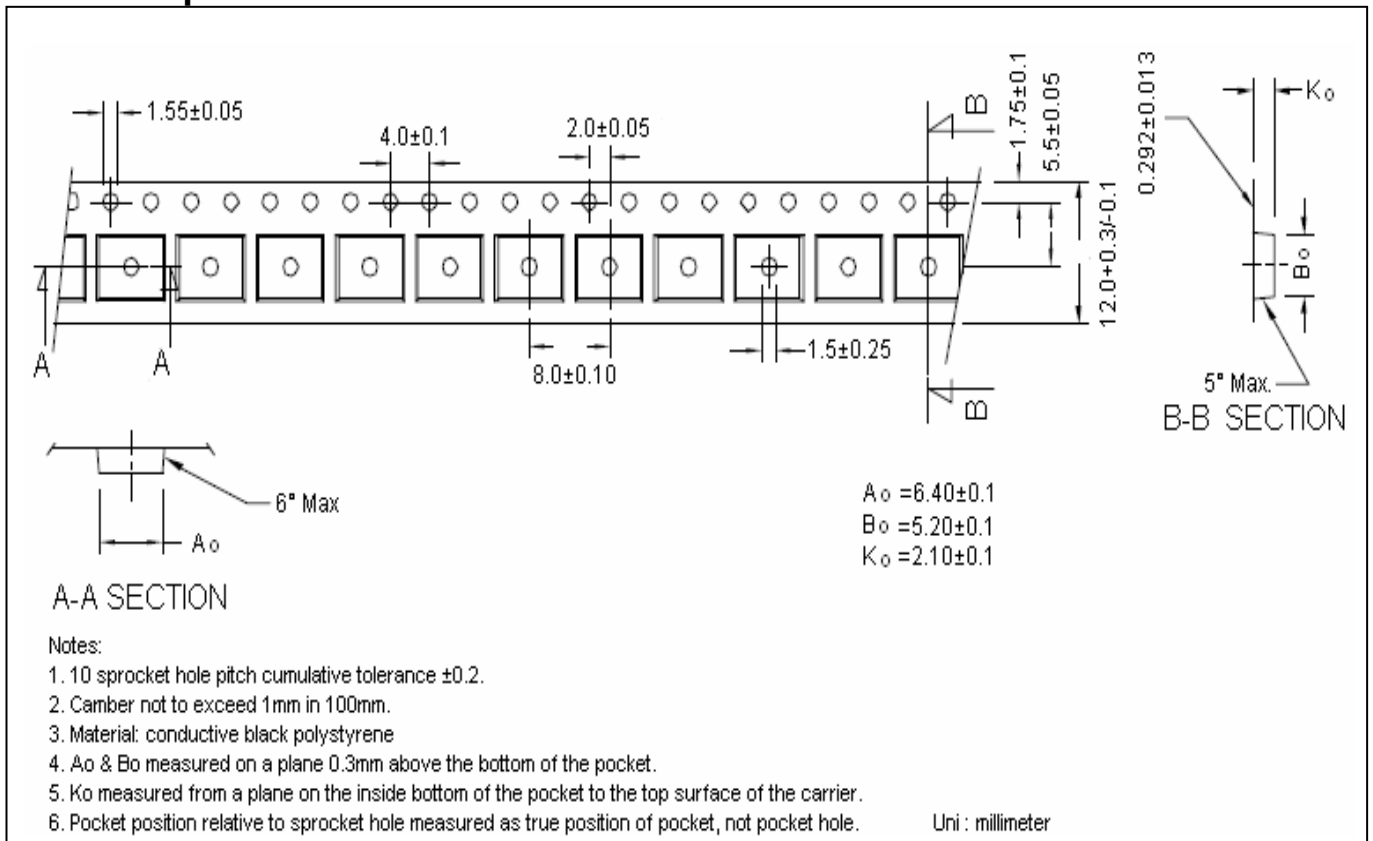
**Characteristic Curves(Cont.)**



**Reel Dimension**



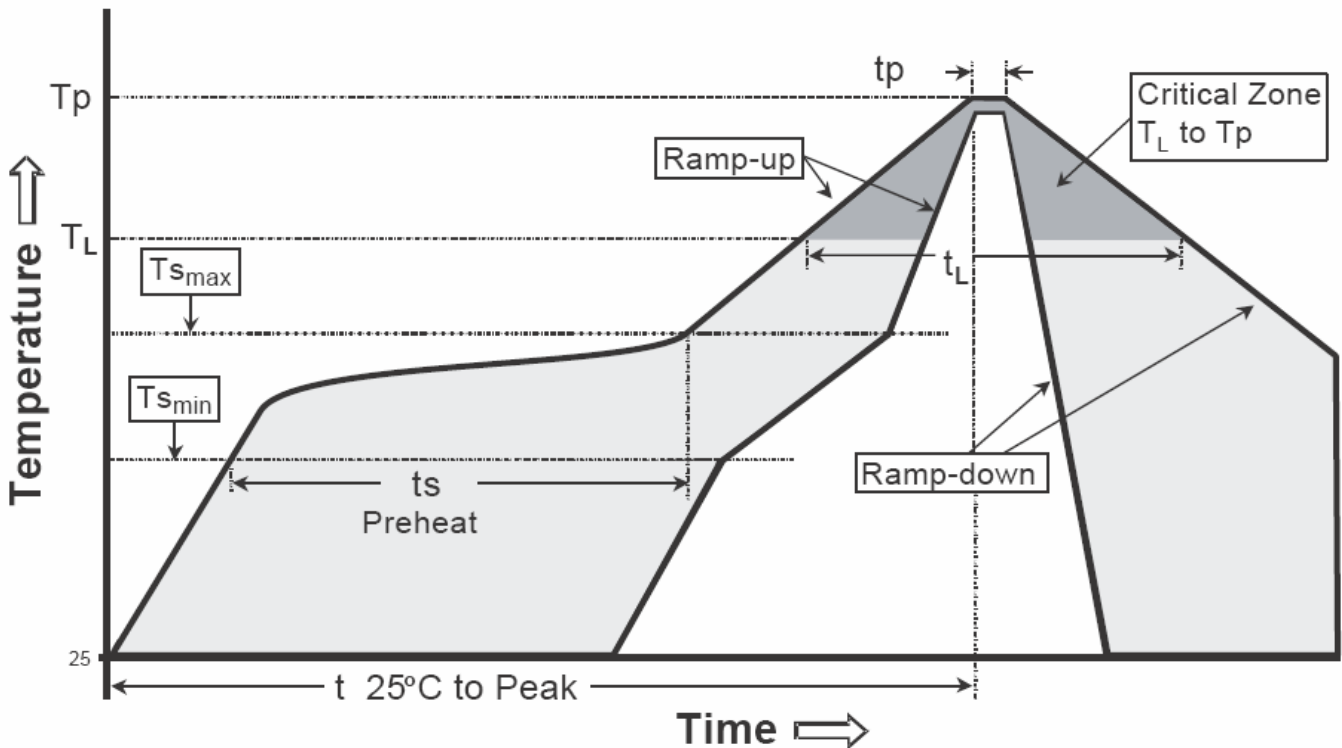
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

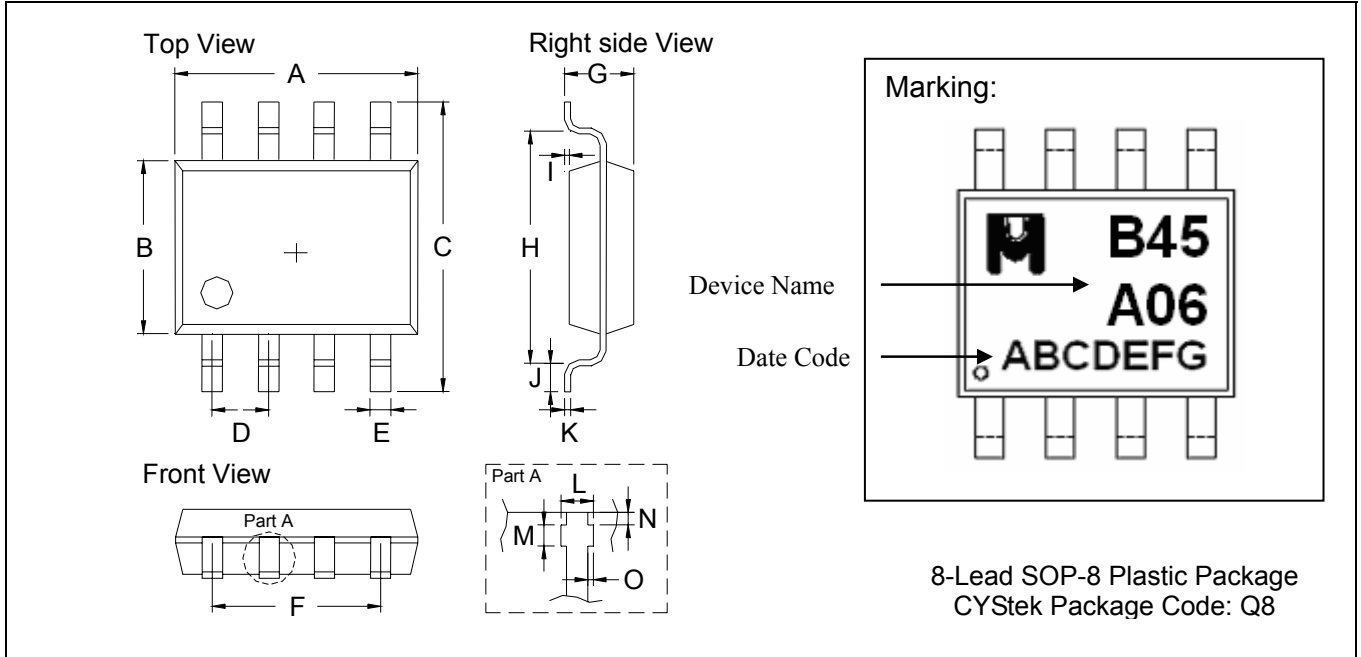
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOP-8 Dimension**



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1909	0.2007	4.85	5.10	I	0.0019	0.0078	0.05	0.20
B	0.1515	0.1555	3.85	3.95	J	0.0118	0.0275	0.30	0.70
C	0.2283	0.2441	5.80	6.20	K	0.0074	0.0098	0.19	0.25
D	0.0480	0.0519	1.22	1.32	L	0.0145	0.0204	0.37	0.52
E	0.0145	0.0185	0.37	0.47	M	0.0118	0.0197	0.30	0.50
F	0.1472	0.1527	3.74	3.88	N	0.0031	0.0051	0.08	0.13
G	0.0570	0.0649	1.45	1.65	O	0.0000	0.0059	0.00	0.15
H	0.1889	0.2007	4.80	5.10					

**Notes:** 1. Controlling dimension: millimeters.  
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: pure tin plated
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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